

REMARKS

Claims 1-27 are pending in this application, with claims 1, 5, 9, 13, 18, and 23 being independent. Claims 1, 5, and 9 have been amended.

Applicants acknowledge with appreciation the Examiner's allowance of claims 9-27. Claim 9 has been amended to add the feature that was added to claims 1 and 5.

Independent claim 1 and dependent claim 3 have been rejected as being anticipated by Mizobata (JP 7-28089). Claim 1, as amended, recites a semiconductor device including "a first electrode; an insulating film formed on said first electrode; ... [and] a second electrode provided on said insulating film; ... wherein *said first electrode overlaps with said second electrode* with said insulating film interposed therebetween" (emphasis added). Applicants request reconsideration and withdrawal of the rejection of claim 1 because Mizobata does not describe or suggest the recited first electrode/second electrode overlapping structure.

As shown in Fig. 3 of Mizobata, the gate electrode 4, which the Examiner equates to the recited first electrode, does not overlap with the pixel electrode 1, which the Examiner equates to the recited second electrode. Accordingly, Mizobata does not describe or suggest the recited first electrode/second electrode overlapping structure, and for at least this reason, applicants request reconsideration and withdrawal of the rejection of claim 1 and its dependent claim 3.

Claims 1-8 have been rejected as being anticipated by Shibata (U.S. Patent No. 6,392,255). Independent claims 1 and 5, as amended, each recite a semiconductor device that includes "a first electrode ... ; an insulating film formed on said first electrode; ... [and] a second electrode provided on *said insulating film*" (emphasis added). Applicants request reconsideration and withdrawal of the rejection of claims 1 and 5 because Shibata does not describe or suggest the recited first electrode/insulating film/second electrode structure.

As shown in Fig. 1 of Shibata, the second insulating film 106, which the Examiner equates to the recited insulating film, is formed on the gate electrode 104, which the Examiner equates to the recited first electrode. However, the electrode 110/pixel electrode 115, which the Examiner equates to the recited second electrode, is not provided on the second insulating film 106, but instead is provided on the third insulating film 108. Accordingly, Shibata does not

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describe or suggest a semiconductor device having the recited first electrode/insulating film/second electrode structure, and, for at least this reason, applicants request reconsideration and withdrawal of the rejection of claims 1 and 5 along with their dependent claims.

Applicants submit that all claims are in condition for allowance.

Enclose is a check for the Petition for Extension of Time fee. Please apply any other charges or credits to deposit account 06-1050.

Respectfully submitted,

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